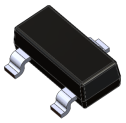
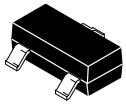
High-Voltage General-Purpose Diode

MMBD1401A, MMBD1403A, MMBD1404A, MMBD1405A



SOT−23
CASE 318BM



SOT−23
CASE 318−08

Description

Sourced from process 2V.

ABSOLUTE MAXIMUM RATINGS

(T_A = 25°C unless otherwise noted) (Notes 2, 3)

Rating	Symbol	Value	Unit
Working Inverse Voltage	W_{IV}	175	V
Average Rectified Current	I_O	200	mA
DC Forward Current	I_F	600	mA
Recurrent Peak Forward Current	i_f	700	mA
Non−Repetitive Peak Forward Surge Current Pulse Width = 1.0 second Pulse Width = 1.0 microsecond	$i_{f(surge)}$	 1.0 2.0	A
Storage Temperature Range	T_{STG}	−55 to +150	°C
Operating Junction Temperature	T_J	150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. These ratings are based on a maximum junction temperature of 150°C.
3. These are steady−state limits. **onsemi** should be consulted on applications involving pulsed or low−duty−cycle operations.

THERMAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted) (Note 4)

Characteristic	Symbol	Value	Unit
Power Dissipation	P_D	350	mW
Derate Above 25°C		2.8	mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	357	°C/W

4. Device is mounted on glass epoxy PCB 1.6 inch × 1.6 inch × 0.06 inch, mounting pad for the collector lead minimum 0.93 in^2.

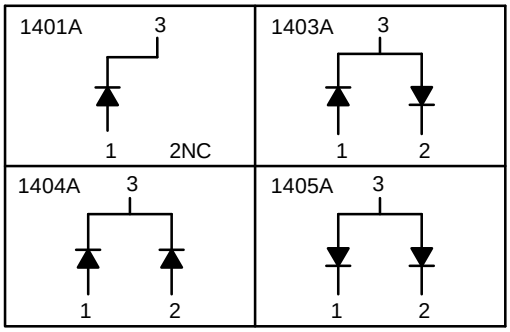
ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

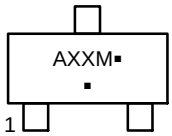
Parameter	Symbol	Condition	Min	Max	Unit
Breakdown Voltage	B_V	I_R = 100 μA	250	−	V
Reverse Current	I_R	V_R = 120 V	−	40	nA
		V_R = 175 V	−	100	nA
Forward Voltage	V_F	I_F = 10 mA	−	800	mV
		I_F = 50 mA	760	920	mV
		I_F = 200 mA	−	1.1	V
		I_F = 300 mA	−	1.25	V
Diode Capacitance	C_O	V_R = 0, f = 1.0 MHz	−	2.0	pF
Reverse Recovery Time	t_{rr}	I_F = I_R = 30 mA, I_{RR} = 3.0 mA, R_L = 100 Ω	−	50	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

CONNECTION DIAGRAMS



MARKING DIAGRAM



AXX = Specific Device Code
XX = 29/32/33/34
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
MMBD1404A	SOT−23 (Pb−Free)	3000 / Tape & Reel

DISCONTINUED (Note 1)

MMBD1401A	SOT−23 (Pb−Free)	3000 / Tape & Reel
MMBD1403A	SOT−23 (Pb−Free)	3000 / Tape & Reel
MMBD1405A	SOT−23 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

1. **DISCONTINUED:** These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.

TYPICAL CHARACTERISTICS

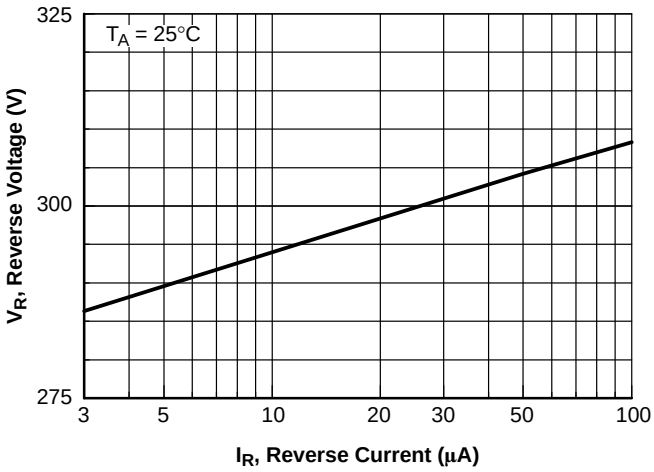


Figure 1. Reverse Voltage vs. Reverse Current
B_V − 1.0 to 100 μA

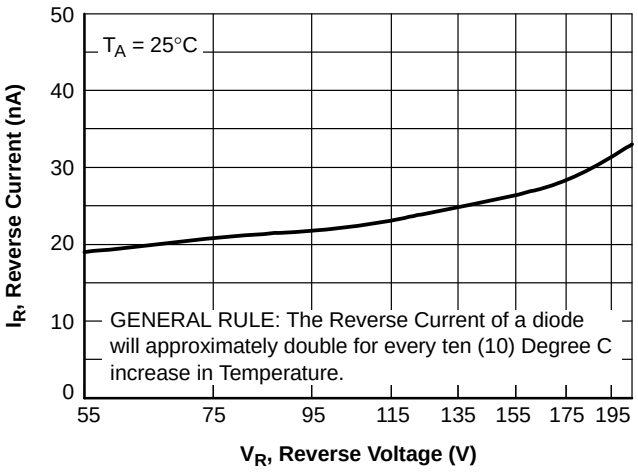


Figure 2. Reverse Current vs. Reverse Voltage
I_R − 55 to 205 V

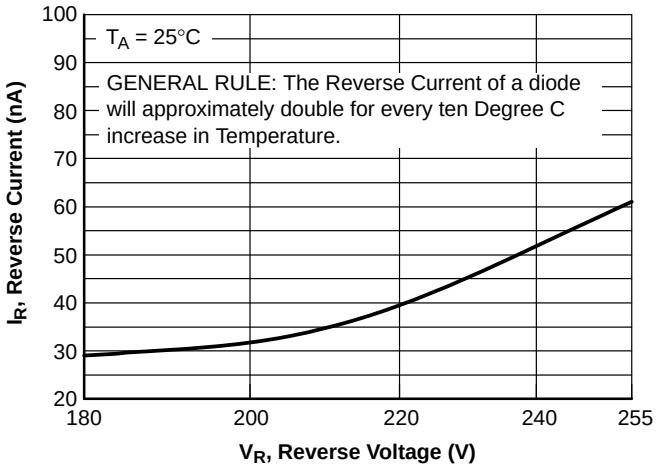


Figure 3. Reverse Current vs. Reverse Voltage
I_R − 180 to 255 V

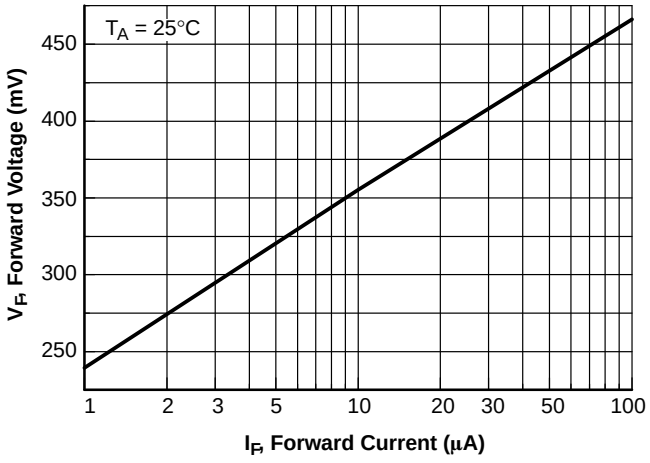


Figure 4. Forward Voltage vs. Forward Current
V_F − 1.0 to 100 μA

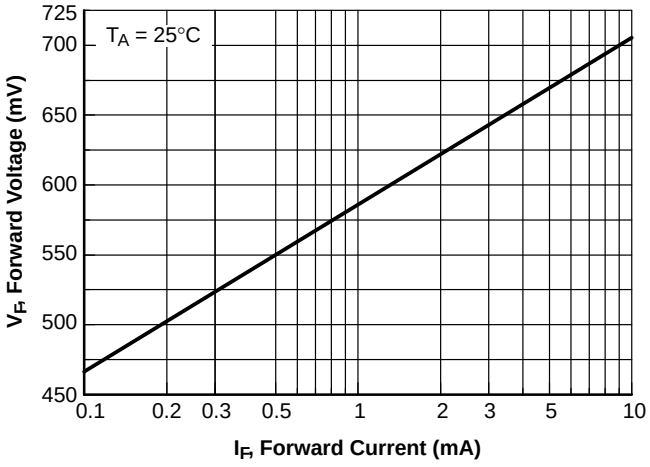


Figure 5. Forward Voltage vs. Forward Current
V_F − 0.1 to 10 mA

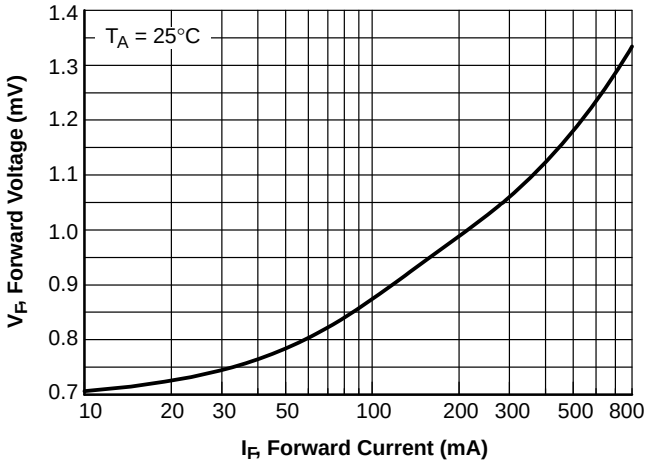


Figure 6. Forward Voltage vs. Forward Current
V_F − 10 to 800 mA

TYPICAL CHARACTERISTICS (Continued)

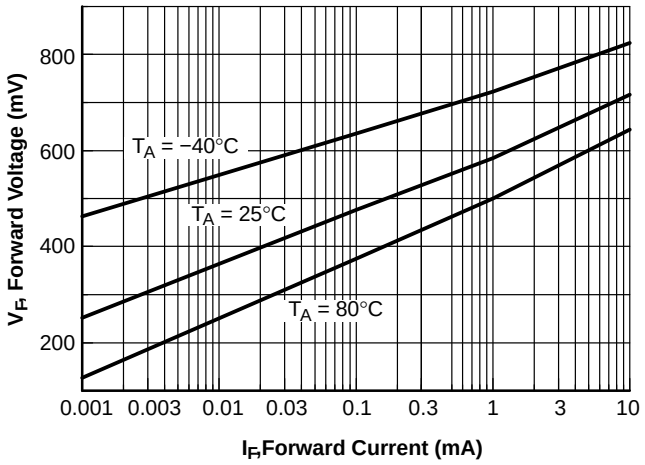


Figure 7. Forward Voltage vs. Ambient Temperature, V_F − 1.0 μA − 10 mA (−40 to +80°C)

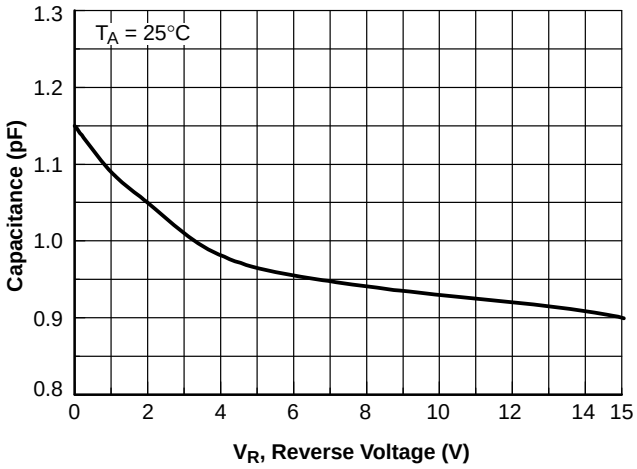


Figure 8. Capacitance vs. Reverse Voltage

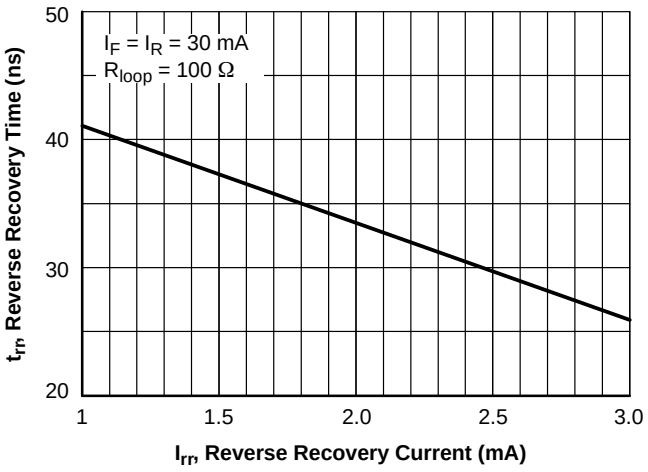


Figure 9. Reverse Recovery Time vs. Reverse Recovery Current (I_{rr})

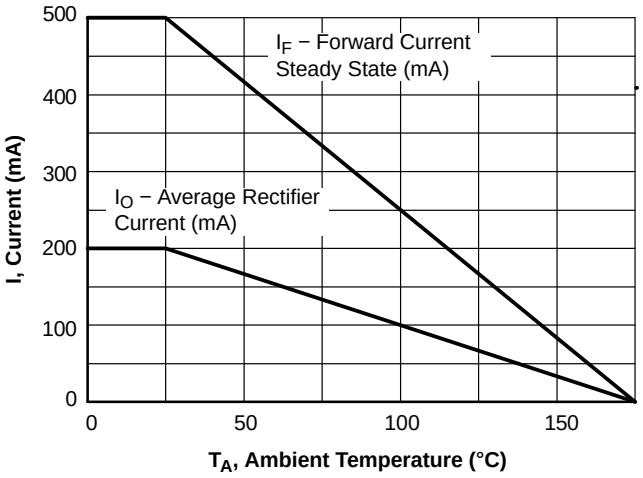


Figure 10. Average Rectified Current (I_O) and Forward Current (I_F) vs. Ambient Temperature (T_A)

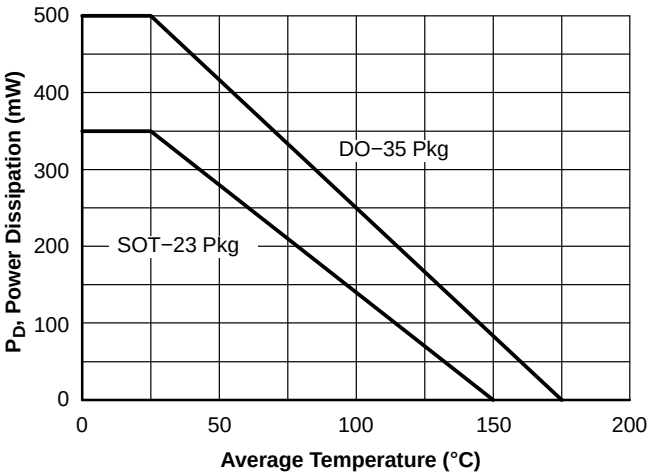
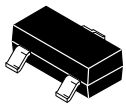


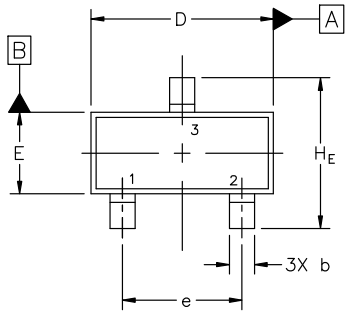
Figure 11. Power Derating Curve



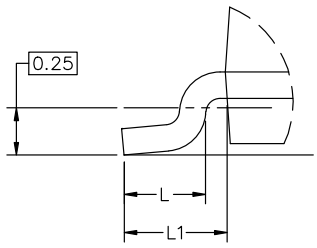
SCALE 4:1

SOT−23 (TO−236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

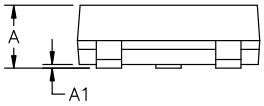
DATE 14 AUG 2024



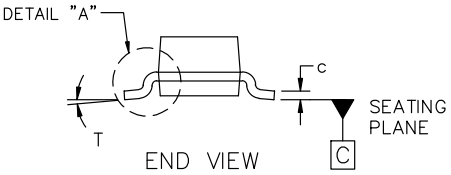
TOP VIEW



DETAIL "A"
Scale 3:1



SIDE VIEW

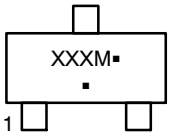


END VIEW

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
H_E	2.10	2.40	2.64
T	0°	−−−	10°

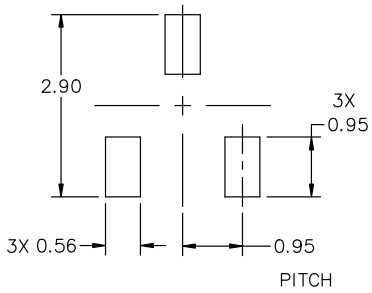
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC
MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb−Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	**98ASB42226B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	**SOT−23 (TO−236) 2.90x1.30x1.00 1.90P**		**PAGE 1 OF 2**

SOT−23 (TO−236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

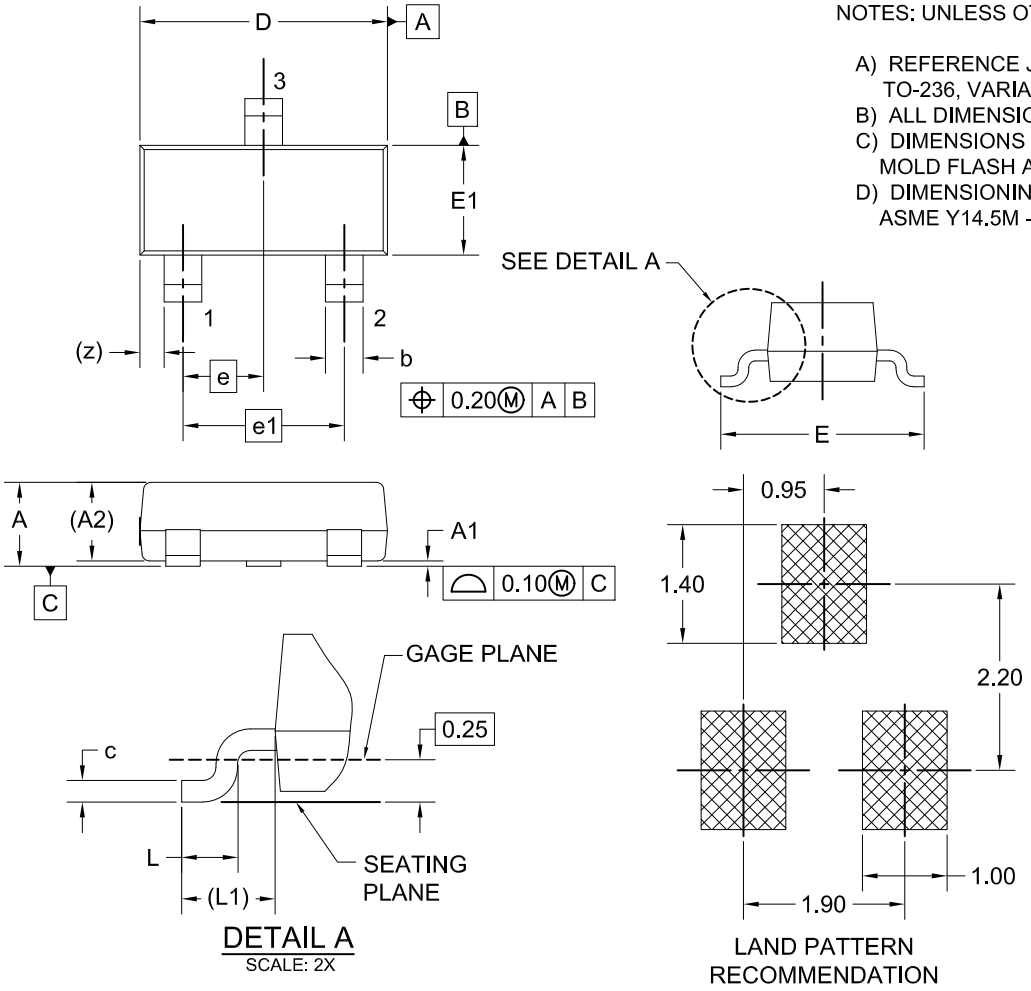
STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

SOT−23
CASE 318BM
ISSUE A

DATE 01 SEP 2021



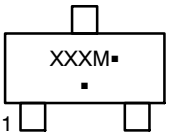
NOTES: UNLESS OTHERWISE SPECIFIED

A) REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE H.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS ARE INCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M - 2009.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.20
A1	0.00	0.05	0.10
A2		0.93 REF	
b	0.37	0.44	0.60
c	0.08	0.15	0.23
D	2.72	2.92	3.12
E	2.10	2.40	2.70
E1	1.15	1.30	1.50
e		0.95 BSC	
e1		1.90 BSC	
L	0.20	---	---
L1		0.55 REF	
z		0.29 REF	

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98AON13784G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	SOT−23	PAGE 1 OF 1

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